

SPTECH Silicon PNP Power Transistor**2SB857****DESCRIPTION**

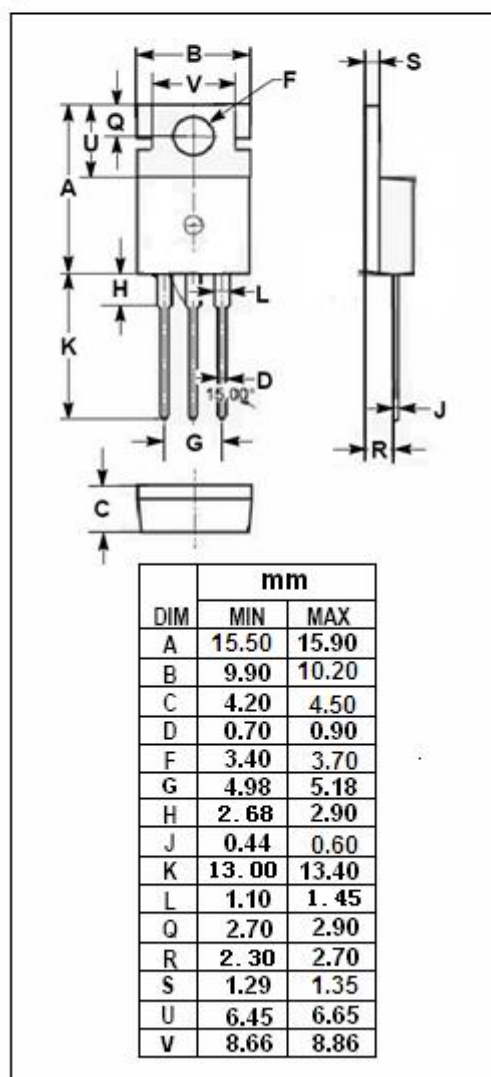
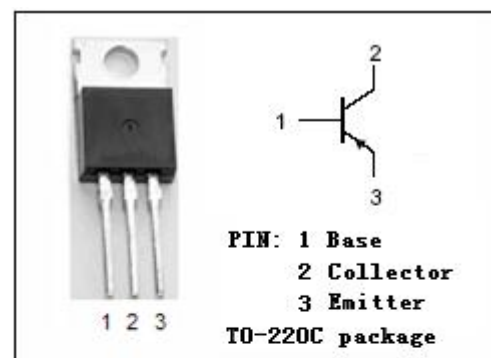
- Collector Current: $I_C = -4A$
- Low Collector Saturation Voltage
: $V_{CE(sat)} = -1.0V(Max)@I_C = -2A$
- High Collector Power Dissipation
- Complement to Type 2SD1133

APPLICATIONS

- Designed for low frequency power amplifier applications.

ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ C$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-70	V
V_{CEO}	Collector-Emitter Voltage	-50	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current-Continuous	-4	A
I_{CM}	Collector Current-Peak	-8	A
P_C	Total Power Dissipation @ $T_C=25^\circ C$	40	W
T_J	Junction Temperature	150	$^\circ C$
T_{stg}	Storage Temperature Range	-45~150	$^\circ C$



SPTECH Silicon PNP Power Transistor**2SB857****ELECTRICAL CHARACTERISTICS****T_C=25°C unless otherwise specified**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	I _C = -30mA ; R _{BE} = ∞	-50			V
V _{(BR)CBO}	Collector-Base Breakdown Voltage	I _C = -1mA ; I _E = 0	-70			V
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	I _E = -1mA ; I _C = 0	-5			V
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = -2A ; I _B = -0.2A			-1.0	V
V _{BE(on)}	Base-Emitter On Voltage	I _C = -1A ; V _{CE} = -4V			-1.0	V
I _{CBO}	Collector Cutoff Current	V _{CB} = -50V ; I _E = 0			-1	μ A
h _{FE-1}	DC Current Gain	I _C = -1A ; V _{CE} = -4V	60		320	
h _{FE-2}	DC Current Gain	I _C = -0.1A ; V _{CE} = -4V	35			
f _T	Current-Gain—Bandwidth Product	I _C = -0.5A ; V _{CE} = -4V		15		MHz

◆ **h_{FE-1} Classifications**

B	C	D
60-120	100-200	160-320